

## Supporting Information

### **Structural and electrical properties of sub-1-nm EOT HfO<sub>2</sub> grown on InAs by atomic layer deposition and its thermal stability**

Yu-Seon Kang<sup>1</sup>, Hang-Kyu Kang<sup>1</sup>, Dae-Kyoung Kim<sup>1</sup>, Kwang-Sik Jeong<sup>1</sup>, Min Baik<sup>1</sup>, Youngseo An<sup>2</sup>, Hyounsub Kim<sup>2</sup>, Jin-Dong Song<sup>3</sup>, Mann-Ho Cho<sup>1,\*</sup>

<sup>1</sup> *Institute of Physics and Applied Physics, Yonsei University, Seoul, 120-749, Korea*

<sup>2</sup> *School Department of Material Science and Engineering, Sungkyunkwan University, Suwon440-746, Korea*

<sup>3</sup> *Center of opto-electronic materials, Korea institute of Science and Technology, Seoul 136-791, Korea*

\*E-mail : mh.cho@yonsei.ac.kr

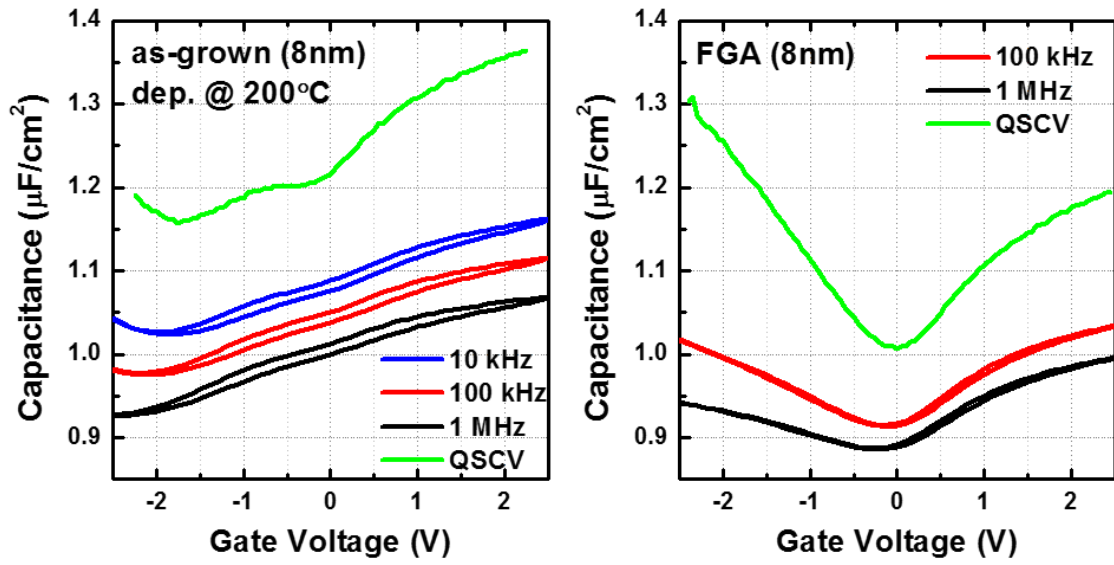


Figure S1. Multi-frequency C-V and quasi-static C-V (QS-CV) characteristics of ALD- HfO<sub>2</sub>/InAs with deposition temperature of 200°C for as-grown (left) and forming gas annealing (FGA) treatment (right).